

NTMS4705N

Power MOSFET

30 V, 12 A, Single N-Channel, SO-8

Features

- Low $R_{DS(on)}$
- Low Gate Charge
- Standard SO-8 Single Package
- Pb-Free Package is Available

Applications

- Notebooks, Graphics Cards
- Synchronous Rectification
- High Side Switch
- DC-DC Converters

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

| Parameter | | | Symbol | Value | Unit |
|---|-------------------------|--------------------------|----------------|------------|------------------|
| Drain-to-Source Voltage | | | V_{DSS} | 30 | V |
| Gate-to-Source Voltage | | | V_{GS} | ± 20 | V |
| Continuous Drain Current (Note 1) | Steady State | $T_A = 25^\circ\text{C}$ | I_D | 10 | A |
| | | $T_A = 85^\circ\text{C}$ | | 7.2 | |
| | $t \leq 10\text{ s}$ | $T_A = 25^\circ\text{C}$ | 12 | | |
| Power Dissipation (Note 1) | Steady State | $T_A = 25^\circ\text{C}$ | P_D | 1.52 | W |
| | $t \leq 10\text{ s}$ | | | 2.3 | |
| Continuous Drain Current (Note 2) | Steady State | $T_A = 25^\circ\text{C}$ | I_D | 7.4 | A |
| | | $T_A = 85^\circ\text{C}$ | | 5.3 | |
| Power Dissipation (Note 2) | | $T_A = 25^\circ\text{C}$ | P_D | 0.85 | W |
| Pulsed Drain Current | $t_p = 10\ \mu\text{s}$ | | I_{DM} | 36 | A |
| Operating Junction and Storage Temperature | | | T_J, T_{stg} | -55 to 150 | $^\circ\text{C}$ |
| Source Current (Body Diode) | | | I_S | 3.0 | A |
| Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 25\text{ V}, V_{GS} = 10\text{ V}, \text{Peak } I_L = 7.5\text{ A}, L = 10\text{ mH}, R_G = 25\ \Omega$) | | | E_{AS} | 210 | mJ |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | | | T_L | 260 | $^\circ\text{C}$ |

THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---|-----------------|-------|--------------------|
| Junction-to-Ambient – Steady State (Note 1) | $R_{\theta JA}$ | 82 | $^\circ\text{C/W}$ |
| Junction-to-Ambient – $t \leq 10\text{ s}$ (Note 1) | $R_{\theta JA}$ | 55 | |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 147 | |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

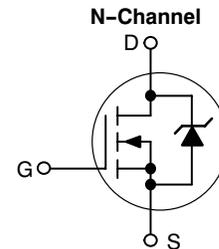
1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface mounted on FR4 board using the minimum recommended pad size.



ON Semiconductor®

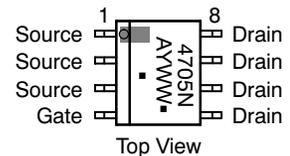
<http://onsemi.com>

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ TYP | I_D MAX (Note 1) |
|---------------|-------------------------|--------------------|
| 30 V | 8.0 m Ω @ 10 V | 12 A |
| | 10.5 m Ω @ 4.5 V | |



SO-8
CASE 751
STYLE 12

MARKING DIAGRAM/ PIN ASSIGNMENT



4705N = Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package
 (Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|----------------|------------------|
| NTMS4705NR2 | SO-8 | 2500/Tape & Reel |
| NTMS4705NR2G | SO-8 (Pb-Free) | 2500/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTMS4705N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|--------------------------------------|--|------------------------|-----|------|-------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0 V, I _D = 250 μA | 30 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V _{(BR)DSS} /T _J | | | 15 | | mV/°C |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V, V _{DS} = 24 V | T _J = 25°C | | 1.0 | μA |
| | | | T _J = 125°C | | 50 | |
| Gate-to-Source Leakage Current | I _{GSS} | V _{DS} = 0 V, V _{GS} = ±20 V | | | ±100 | nA |

ON CHARACTERISTICS (Note 3)

| | | | | | | |
|--|-------------------------------------|---|-----|------|-----|-------|
| Gate Threshold Voltage | V _{GS(TH)} | V _{GS} = V _{DS} , I _D = 250 μA | 1.0 | | 2.5 | V |
| Negative Threshold Temperature Coefficient | V _{GS(TH)} /T _J | | | 5.0 | | mV/°C |
| Drain-to-Source On Resistance | R _{DS(on)} | V _{GS} = 10 V, I _D = 12 A | | 8.0 | 10 | mΩ |
| | | V _{GS} = 4.5 V, I _D = 10 A | | 10.5 | 14 | |
| Forward Transconductance | g _{FS} | V _{DS} = 15 V, I _D = 10 A | | 19 | | S |

CHARGES, CAPACITANCES AND GATE RESISTANCE

| | | | | | | |
|------------------------------|---------------------|--|--|------|-----|----|
| Input Capacitance | C _{iss} | V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 24 V | | 1078 | | pF |
| Output Capacitance | C _{oss} | | | 460 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 127 | | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 10 A | | 11 | 18 | nC |
| Threshold Gate Charge | Q _{G(TH)} | | | 1.1 | | |
| Gate-to-Source Charge | Q _{GS} | | | 2.1 | | |
| Gate-to-Drain Charge | Q _{GD} | | | 5.8 | | |
| Gate Resistance | R _G | | | 1.76 | 3.5 | |

SWITCHING CHARACTERISTICS (Note 4)

| | | | | | | |
|---------------------|---------------------|--|--|-----|--|----|
| Turn-On Delay Time | t _{d(on)} | V _{GS} = 10 V, V _{DD} = 15 V, I _D = 1.0 A, R _G = 3.0 Ω | | 7.8 | | ns |
| Rise Time | t _r | | | 4.7 | | |
| Turn-Off Delay Time | t _{d(off)} | | | 27 | | |
| Fall Time | t _f | | | 17 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|-----------------|---|------------------------|----|------|-----|----|
| Forward Diode Voltage | V _{SD} | V _{GS} = 0 V, I _S = 3.0 A | T _J = 25°C | | 0.73 | 1.0 | V |
| | | | T _J = 125°C | | 0.51 | | |
| Reverse Recovery Time | t _{RR} | V _{GS} = 0 V, dI _S /d _t = 100 A/μs, I _S = 3.0 A | | 38 | | ns | |
| Charge Time | t _a | | | 17 | | | |
| Discharge Time | t _b | | | 21 | | | |
| Reverse Recovery Charge | Q _{RR} | | | 30 | | | nC |

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

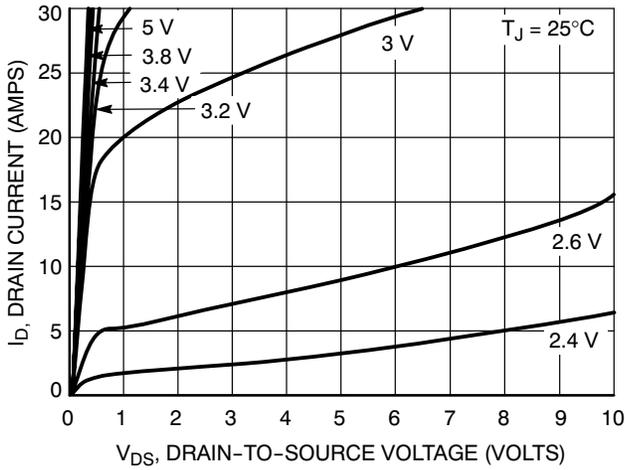


Figure 1. On-Region Characteristics

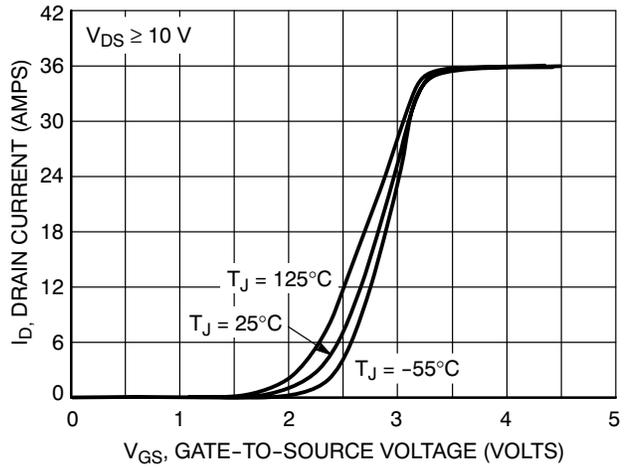


Figure 2. Transfer Characteristics

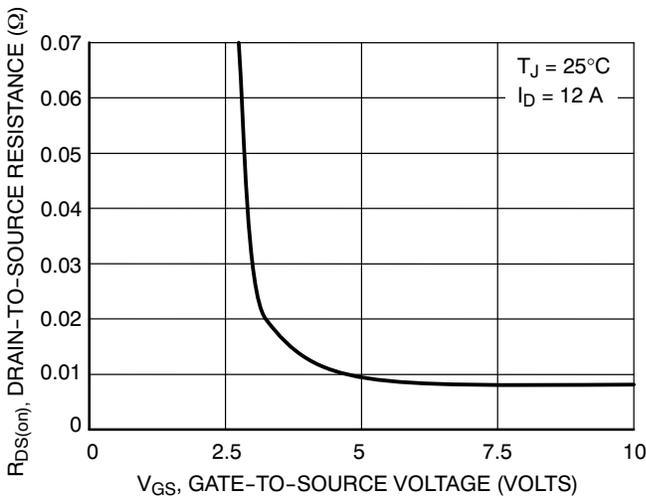


Figure 3. On-Resistance vs. Gate-to-Source Voltage

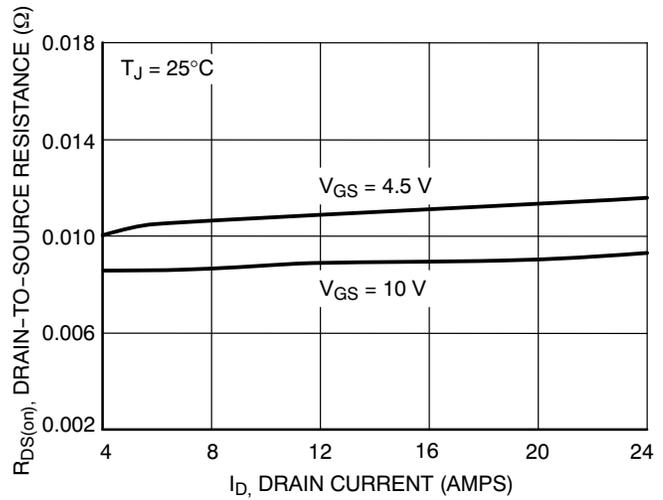


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

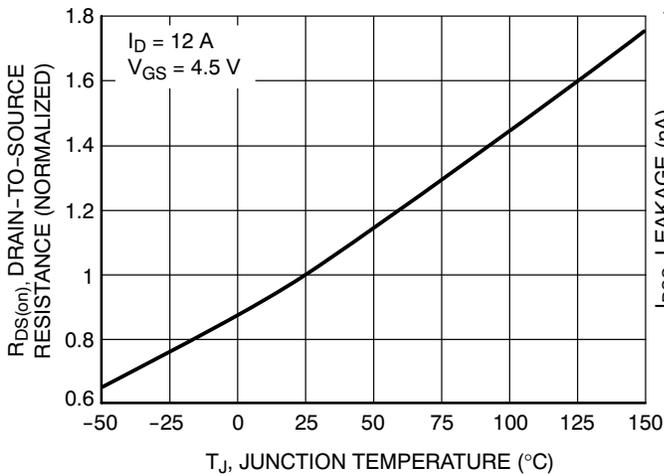


Figure 5. On-Resistance Variation with Temperature

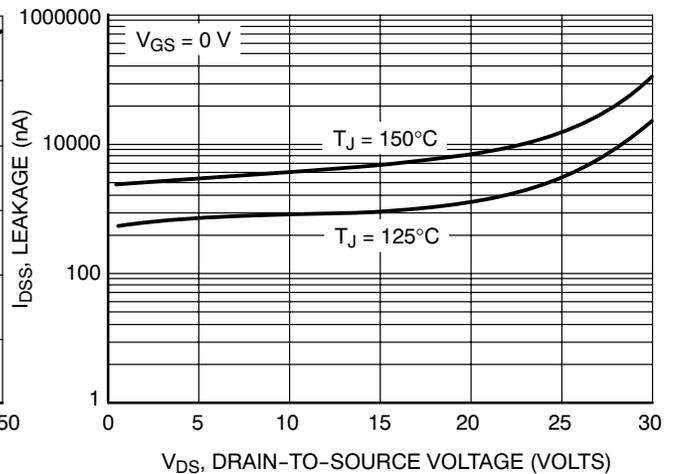


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL PERFORMANCE CURVES

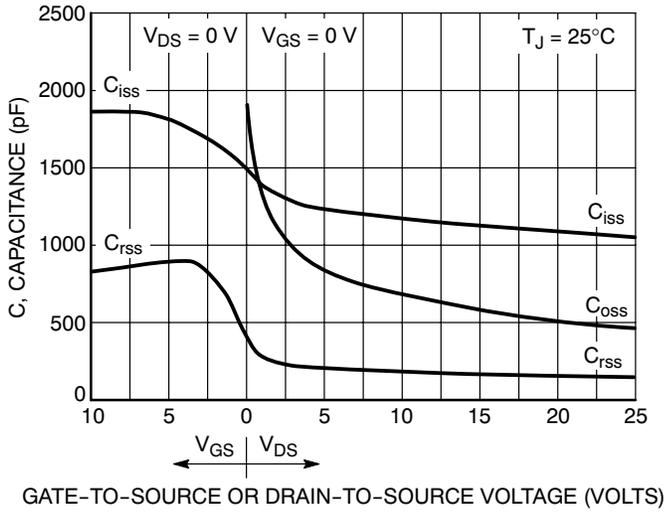


Figure 7. Capacitance Variation

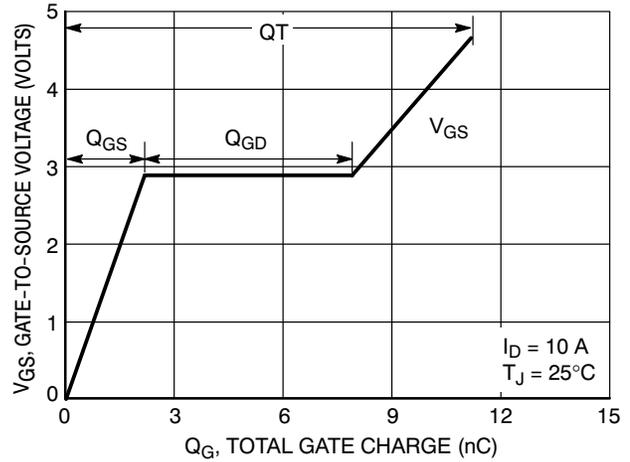


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

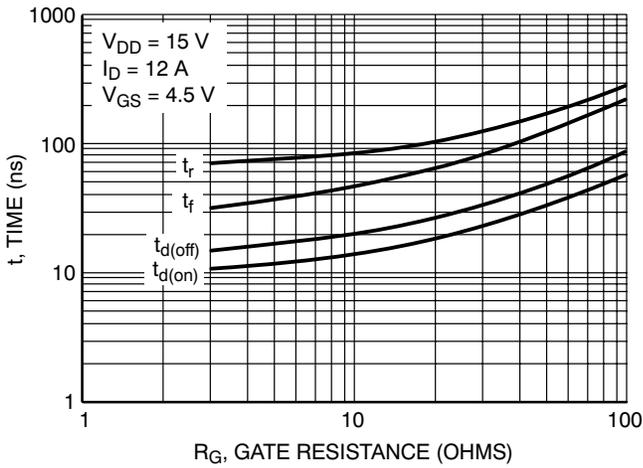


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

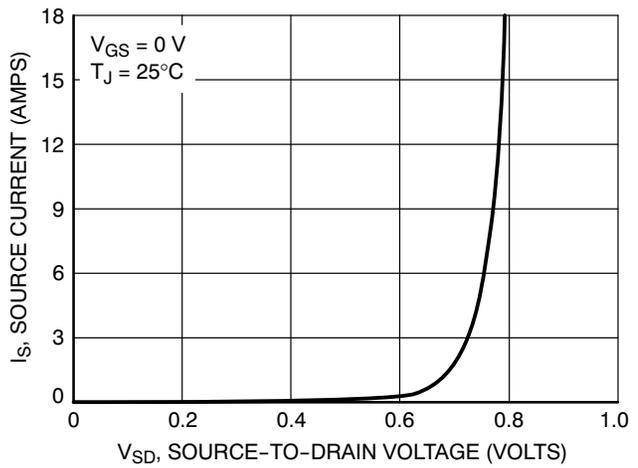


Figure 10. Diode Forward Voltage vs. Current

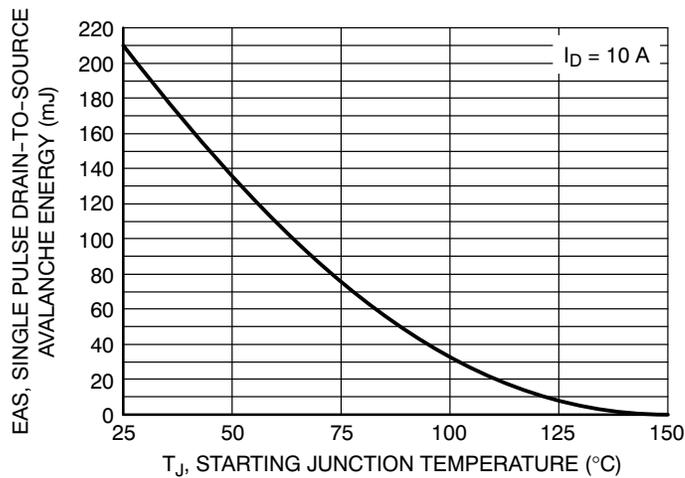
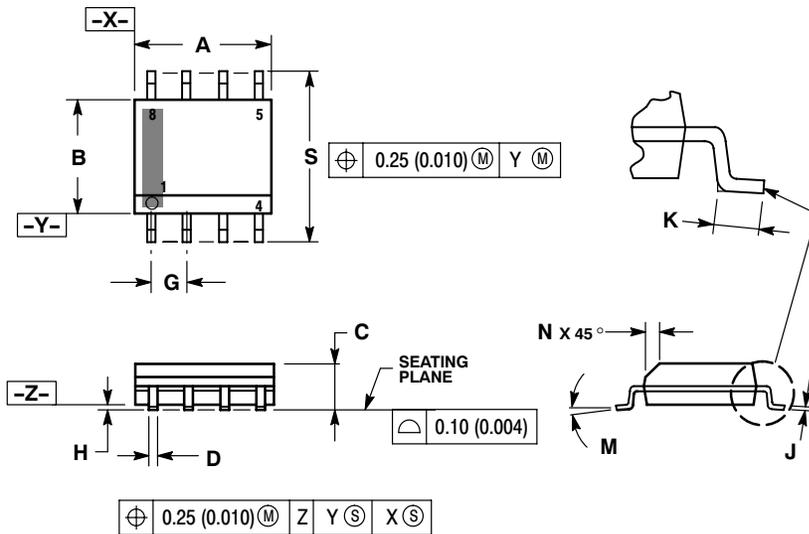


Figure 11. Maximum Avalanche Energy vs. Starting Junction Temperature

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PACKAGE DIMENSIONS

SOIC-8
CASE 751-07
ISSUE AJ



NOTES:

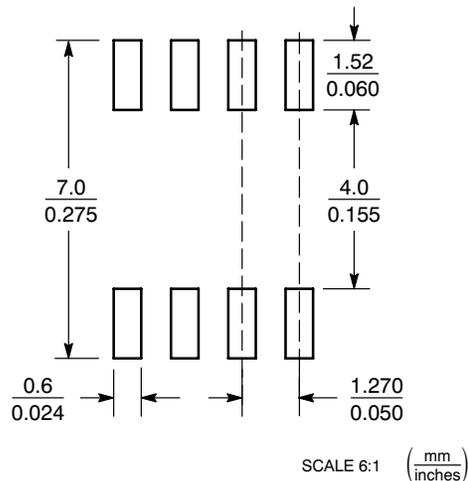
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC | | 0.050 BSC | |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0° | 8° | 0° | 8° |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

STYLE 12:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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